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**IN THE CLAIMS**

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1. (Currently Amended) A method of forming a gate oxide on a transistor body region, comprising:

evaporation depositing a metal alloy layer on the body region wherein at least a portion of the alloy layer is amorphous; and

oxidizing the metal alloy layer to form a metal oxide layer on the body region.

2. (Original) The method of claim 1, wherein evaporation depositing the metal alloy layer includes evaporation depositing cobalt and titanium.

3. (Original) The method of claim 1, wherein evaporation depositing the metal alloy layer includes evaporation depositing by electron beam evaporation.

4. (Original) The method of claim 3, wherein electron beam evaporation depositing the metal alloy layer includes electron beam evaporation of a single metal alloy target.

5. (Original) The method of claim 1, wherein evaporation depositing the metal alloy layer includes evaporation depositing at an approximate substrate temperature range of 100 - 150° C.

6. (Original) The method of claim 1, wherein oxidizing the metal alloy layer includes oxidizing at a temperature of approximately 400° C.

7. (Original) The method of claim 1, wherein oxidizing the metal alloy layer includes oxidizing with atomic oxygen.

8. (Original) The method of claim 1, wherein oxidizing the metal alloy layer includes oxidizing using a krypton (Kr)/oxygen (O<sub>2</sub>) mixed plasma process.

9. (Currently Amended) A method of forming a gate oxide on a transistor body region, comprising:

evaporation depositing a metal alloy layer on the body region wherein at least a portion of the alloy layer is amorphous; and

oxidizing the metal alloy layer using a krypton(Kr)/oxygen ( $\text{O}_2$ ) mixed plasma process to form a metal oxide layer on the body region.

10. (Original) The method of claim 9, wherein evaporation depositing the metal alloy layer includes evaporation depositing cobalt and titanium.

11. (Original) The method of claim 9, wherein evaporation depositing the metal alloy layer includes evaporation depositing by electron beam evaporation.

12. (Original) The method of claim 11, wherein electron beam evaporation depositing the metal alloy layer includes electron beam evaporation of a single metal alloy target.

13. (Original) The method of claim 9, wherein evaporation depositing the metal alloy layer includes evaporation depositing at an approximate substrate temperature range of 150 - 400 °C.

14. - 54. (Previously Withdrawn)

55. (Currently Amended) A method of forming a gate oxide on a transistor body region, comprising:

electron beam evaporation depositing a metal alloy layer on the body region wherein at least a portion of the alloy layer is amorphous; and

oxidizing the metal alloy layer to form a metal oxide layer on the body region.

56. (New) A method of forming a gate oxide on a transistor body region, comprising: evaporation depositing an alloy layer including cobalt and titanium on the body region;

and

oxidizing the metal alloy layer to form a metal oxide layer on the body region.

57. (New) The method of claim 56, wherein oxidizing the metal alloy layer includes oxidizing with atomic oxygen.
58. (New) The method of claim 56, wherein oxidizing the metal alloy layer includes oxidizing using a krypton (Kr)/oxygen (O<sub>2</sub>) mixed plasma process.
59. (New) A method of forming a gate oxide on a transistor body region, comprising:  
evaporation depositing an alloy layer including cobalt and titanium on the body region;  
and  
oxidizing the metal alloy layer using a krypton(Kr)/oxygen (O<sub>2</sub>) mixed plasma process to form a metal oxide layer on the body region.
60. (New) The method of claim 59, wherein evaporation depositing the metal alloy layer includes evaporation depositing by electron beam evaporation.
61. (New) The method of claim 59, wherein electron beam evaporation depositing the metal alloy layer includes electron beam evaporation of a single metal alloy target.
62. (New) A method of forming a gate oxide on a transistor body region, comprising:  
evaporation depositing an alloy layer including cobalt and titanium on the body region wherein at least a portion of the alloy layer is amorphous; and  
oxidizing the metal alloy layer to form a metal oxide layer on the body region.
63. (New) The method of claim 62, wherein evaporation depositing the metal alloy layer includes evaporation depositing by electron beam evaporation.
64. (New) The method of claim 62, wherein electron beam evaporation depositing the metal alloy layer includes electron beam evaporation of a single metal alloy target.

65. (New) A method of forming a gate oxide on a transistor body region, comprising:  
evaporation depositing an alloy layer including cobalt and titanium on the body region  
wherein at least a portion of the alloy layer is amorphous; and  
oxidizing the metal alloy layer using a krypton(Kr)/oxygen (O<sub>2</sub>) mixed plasma process to  
form a metal oxide layer on the body region.
66. (New) The method of claim 65, wherein oxidizing the metal alloy layer includes  
oxidizing with atomic oxygen.
67. (New) The method of claim 65, wherein oxidizing the metal alloy layer includes  
oxidizing using a krypton (Kr)/oxygen (O<sub>2</sub>) mixed plasma process.